

Cite this article: Naman, Review of bottom-up and top-down nanofabrication techniques, *RP Cur. Tr. Appl. Sci.* **2** (2023) 73–77.

Review Article

Review of bottom-up and top-down nanofabrication techniques

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ARTICLE HISTORY

ABSTRACT

Received: 30 June 2023 Revised: 30 August 2023 Accepted: 31 August 2023 Published online: 16 Sept. 2023

KEYWORDS

Nanofabrication; Bottomup methods; Top-down methods; Atomic layer deposition' Nanofabrication; Lithography.

Advancements in various fields, including electronics, photonics, and biomedical applications, are made possible by the production and manipulation of nanoscale structures, which is made possible by nanofabrication techniques. Nanofabrication today is done using two different techniques: bottom-up and top-down. The ideas, benefits, and applications of bottom-up and top-down nanofabrication techniques are examined in this review of the literature. The review starts out with a description of bottom-up nanofabrication methods, which entail assembling and synthesizing nanoscale structures out of smaller constituent parts. The ability to create complex nanostructures with exact control over composition, morphology, and size is highlighted by the exploration of a number of techniques including self-assembly, atomic-layer deposition. Bottom-up approaches, benefits and drawbacks, including those related to scalability and reproducibility, are examined along with their uses in nanoelectronics, nanophotonics, and nanomedicine. The article then goes into top-down nanofabrication methods, which entail modifying bigger structures to produce characteristics at the nanoscale. Among the popular methods covered in this area are different lithography techniques like photolithography and electron-beam lithography. Their operating principles, resolution capacities, and fabrication constraints are briefly discussed by the review. The top-down and bottom-up techniques are contrasted in order to show their relative advantages and disadvantages. It is also investigated how bottom-up and top-down strategies might work together to form hybrid nanofabrication methods that take advantage of the best aspects of both approaches. Concluding with discussion of nanofabrication's present tendencies and potential in the future. It is underlined how improvements in nanofabrication methods could spur innovations in fields including nanoelectronics, energy storage, and biosensing.

1. Introduction

Nanofabrication methods include various different techniques used for fabricating and manufacturing nano structures i.e. structures that are of nano scale which is usually less than 10 nm. Nanofabrication involves the precise manipulation and assembly of materials at the nanoscale, and it is used to build devices and structures with distinct characteristics. It is a multidisciplinary field that incorporates ideas from physics, chemistry, engineering, and materials science to create structures with average sizes between one and hundreds of nanometers. The development of numerous applications, such as electronics, energy, medicine, and materials science, depends on the use of nanofabrication techniques. They make it possible to create customized nanoscale materials and technologies, including nanoelectronics. nanosensors, nanophotonics, and nanostructured materials. The top-down and bottom-up methods of nanofabrication are the two main strategies. Each approach has unique benefits and is used in various industrial processes.

2. Bottom-up nanofabrication techniques

Bricklaying serves as a good illustration of bottom-up methods because it builds larger structures (nanostructure) by laying out smaller ones (atoms, molecules) in a similar way. Bottom-up methods entail assembling and synthesizing individual atoms, molecules, or nanoparticles into nanostructures. These methods assemble complex structures layer by layer through the use of molecular recognition, selfassembly, and chemical reactions. Atomic-layer deposition (ALD), sol-gel, chemical vapour deposition (CVD), molecular beam epitaxy (MBE), and self-assembly procedures are a few examples of frequently used bottom-up techniques.

Self-assembly is a powerful bottom-up nanofabrication technique that enables the spontaneous organization of nanoscale building blocks into functional structures and devices. This process relies on the inherent properties of the building blocks, such as their shape, size, and surface interactions, to guide their assembly into desired configurations. Self-assembly has garnered significant attention in the field of nanotechnology due to its potential for scalable and cost-effective fabrication of complex nanostructures with precise control over their properties. Advancements and applications of self-assembly in bottom-up nanofabrication are discussed below.

2.1 Advancements in self-assembly techniques

DNA Origami: DNA molecules have emerged as versatile building blocks for self-assembly due to their programmability and complementary base pairing. DNA origami, a technique



pioneered by Rothemund in 2006, allows the folding of long single-stranded DNA into predefined nanostructures with remarkable precision. DNA origami has been used to create a wide range of nanostructures, including nanoscale boxes, cages, and arrays, with applications in drug delivery, biosensing, and nanoelectronics [2-4].

Block Copolymer Self-Assembly: Block copolymers, consisting of two or more chemically distinct polymer blocks, exhibit microphase separation upon self-assembly. By controlling the composition and molecular weight of the blocks, it is possible to engineer nanoscale patterns with high regularity. Advances in block copolymer lithography have enabled the fabrication of nanoscale features with sub-10 nm dimensions, offering potential applications in nanoelectronics and nanophotonics [5-6].

Colloidal Self-Assembly: Colloidal particles suspended in a solvent can self-assemble into ordered structures driven by various forces, such as electrostatic, van der Waals, and magnetic interactions. The precise control over particle size, shape, and surface properties allows for the fabrication of complex structures, including colloidal crystals, photonic crystals, and metamaterials. Colloidal self-assembly has found applications in optics, photonics, and energy conversion [7].

2.2 Applications of self-assembly in nanofabrication

Nanoelectronics: Self-assembly techniques have been utilized to fabricate nanoscale electronic devices and circuits. DNA origami has been employed to position metallic nanoparticles with nanometer precision, enabling the development of plasmonic devices for enhanced light-matter interactions. Block copolymer lithography has been used to create nanoscale patterns for the fabrication of high-density memory devices and transistors [8].

Nanomedicine: Self-assembly holds great promise in the field of nanomedicine for drug delivery systems and tissue engineering. Self-assembled nanocarriers, such as liposomes and micelles, can encapsulate drugs and target specific cells or tissues. DNA-based self-assembled nanostructures have been explored for gene delivery and as biosensors for disease detection [4].

Energy Applications: Self-assembly has been applied in energy conversion and storage devices. For instance, selfassembled nanoparticle arrays can enhance the efficiency of solar cells by trapping light and promoting charge transport. Self-assembled nanostructured electrodes have been investigated for high-capacity batteries and supercapacitors [9].

Self-assembly is a versatile and promising bottom-up nanofabrication technique that offers precise control over the assembly of nanoscale building blocks. Advances in selfassembly techniques, such as DNA origami, block copolymer self-assembly, and colloidal self-assembly, have facilitated the fabrication of complex nanostructures with tailored properties. The applications of self-assembly span various fields, nanoelectronics, nanomedicine, and energy. including Continued research and development in self-assembly potential techniques hold the for revolutionizing nanofabrication and enabling the creation of advanced nanoscale devices and materials with enhanced functionalities.

Atomic Layer Deposition: Atomic Layer Deposition (ALD) is a versatile and powerful bottom-up nanofabrication

technique that allows precise control over the deposition of thin films at the atomic level. ALD has gained significant attention and has become an integral part of the nanofabrication toolbox due to its unique ability to produce conformal and uniform coatings on complex three-dimensional (3D) structures. In this literature review, we explore the advancements and applications of ALD as a bottom-up nanofabrication technique.

Principles of ALD: ALD is based on sequential selflimiting surface reactions, where precursors are introduced one at a time to react with the substrate surface. These precursors undergo chemisorption and react with the substrate surface to form a monolayer. The process is then repeated, alternating between precursors, to grow a desired film thickness with atomic precision. The self-limiting nature of the reactions ensures controlled and uniform growth, even on high aspect ratio structures [10].

2.3 Advancements in ALD techniques

New Precursors: One significant advancement in ALD is the development of new precursors that offer enhanced reactivity and film properties. Precursor design plays a critical role in achieving desired film characteristics such as composition, stoichiometry, and purity. The introduction of novel precursors with improved reactivity and stability has expanded the range of materials that can be deposited using ALD.

Plasma-Assisted ALD: Plasma-enhanced ALD (PEALD) involves the use of plasma to enhance the precursor reactivity and enable lower process temperatures. PEALD offers faster deposition rates and improved film properties compared to thermal ALD. It has been particularly useful for depositing nitrides, oxides, and other challenging materials.

Area-Selective ALD: Area-selective ALD allows selective deposition of thin films on predefined areas, enabling precise patterning and integration of different materials. This approach is crucial for fabricating complex nanoscale devices, such as transistors and memory devices, where controlled deposition on specific regions is necessary.

2.4 Applications of ALD in nanofabrication

Semiconductor Devices: ALD plays a vital role in semiconductor fabrication, enabling the deposition of high-quality gate dielectrics, diffusion barriers, and metal contacts. It helps improve device performance, reduce power consumption, and enhance reliability.

Energy Storage and Conversion: ALD is extensively used in the development of energy storage devices, such as lithiumion batteries and supercapacitors. It enables the formation of thin protective coatings, improved electrode-electrolyte interfaces, and tailored nanostructures for enhanced performance.

Catalysis: ALD allows precise control over catalyst composition, structure, and active site distribution. It has been employed to fabricate catalysts with high activity, selectivity, and durability for various applications, including fuel cells, hydrogen generation, and chemical synthesis.

Optoelectronics and Photonics: ALD is used to fabricate thin films and nanostructures for optoelectronic devices, such as photovoltaics, light-emitting diodes (LEDs), and optical

coatings. It enables the creation of high-quality films with excellent optical properties and conformal coverage.

ALD has emerged as a powerful bottom-up nanofabrication technique, offering atomic-level control over film deposition and enabling the fabrication of complex nanoscale structures. Advances in precursor design, plasmaassisted processes, and area-selective ALD have expanded the capabilities of ALD, enabling deposition of a wide range of materials with tailored properties. Its applications in semiconductor devices, energy storage, catalysis, and optoelectronics highlight the versatility and importance of ALD in various fields. Further advancements in ALD techniques and precursor materials will continue to drive innovation in nanofabrication and unlock new opportunities for developing advanced nanoscale devices and materials [10].

2.5 Advantages of bottom-up techniques

Atomic precision: Bottom-up techniques allow precise control over the arrangement and composition of nanostructures at the atomic or molecular level.

Scalability: These techniques have the potential for high scalability, enabling the production of large quantities of nanomaterials or nanostructures.

Design flexibility: Bottom-up techniques offer the ability to create complex and intricate structures that are challenging to achieve using top-down methods.

3. Top-down nanofabrication techniques

Top-down techniques involve the fabrication of nanostructures by reducing the size of larger structures through etching, milling, or lithographic processes. These techniques start with a larger material or device and selectively remove or shape it to create the desired nanostructure. Common examples of top-down techniques include photolithography, electron beam lithography, and focused ion beam milling [11].

Photolithography: Photolithography is a fundamental topdown nanofabrication technique that has revolutionized the semiconductor industry and played a pivotal role in the development of modern electronic devices. It involves the use of light to transfer a pattern onto a photosensitive material, enabling precise patterning of nanoscale structures on a substrate. This literature review provides an overview of the advancements, challenges, and applications of photolithography in top-down nanofabrication.

3.1 Advancements in photolithography techniques

Optical Lithography: Traditional optical lithography, using ultraviolet (UV) light, has been the workhorse of the semiconductor industry. The continuous advancements in lens designs, photoresists, and exposure tools have allowed the fabrication of smaller feature sizes and higher device densities. However, as feature sizes approach the deep sub-wavelength regime, optical limitations have led to the exploration of alternative techniques.

Extreme Ultraviolet Lithography (EUV): EUV lithography employs a significantly shorter wavelength (13.5 nm) compared to traditional optical lithography, enabling the fabrication of smaller features. It involves complex optics, reflective masks, and highly sensitive photoresists. EUV

lithography has been a major focus of research and development to extend the limits of top-down nanofabrication.

Nanoimprint Lithography (NIL): NIL utilizes a template or mold with nanoscale features to imprint the desired pattern onto a resist layer. This technique offers high resolution, low cost, and high throughput. Advances in NIL have enabled the fabrication of sub-10 nm features and its integration with other nanofabrication methods, such as self-assembly and directed assembly, to achieve complex structures.

3.2 Challenges in photolithography

Resolution Limitations: The diffraction of light imposes a fundamental limit on the achievable resolution of photolithography. Overcoming this limitation requires the use of techniques such as optical proximity correction, phase-shifting masks, and resolution enhancement technologies to improve pattern fidelity and resolution.

Cost and Complexity: As feature sizes shrink, the cost of photolithography equipment and mask fabrication increases substantially. The complexity of the lithographic process, including alignment, exposure, and development steps, poses challenges in terms of process control, yield, and cost-effective manufacturing.

Edge Roughness: At the nanoscale, the roughness of pattern edges becomes a critical issue. The variations in resist thickness, diffusion of photoactive compounds, and sidewall roughness contribute to edge roughness, which can degrade device performance. Researchers are exploring various techniques, including advanced resist materials and smoothing processes, to mitigate this issue.

3.3 Applications of photolithography in nanofabrication

Semiconductor Device Fabrication: Photolithography is the cornerstone of semiconductor manufacturing, enabling the production of integrated circuits, transistors, and memory devices. It plays a vital role in defining device architectures and interconnects with high precision and accuracy.

Micro- and Nanoelectromechanical Systems (*MEMS/NEMS*): Photolithography is extensively employed in the fabrication of MEMS/NEMS devices, which include sensors, actuators, and microfluidic devices. It enables the precise patterning of structures and functional elements necessary for their operation.

Optoelectronic Devices: Photolithography is instrumental in fabricating optoelectronic devices, such as light-emitting diodes (LEDs), photodetectors, and waveguides. It enables the precise positioning and patterning of materials to achieve efficient light manipulation and device integration. Photolithography has been a crucial top-down nanofabrication technique, driving advancements in the semiconductor industry and various fields of nanotechnology. While traditional optical lithography has made significant progress, emerging techniques such as EUV lithography and nanoimprint lithography offer new possibilities for pushing the boundaries of nanoscale patterning. Overcoming challenges related to resolution, cost, and edge roughness remains essential for the continued progress of photolithography. The applications of photolithography in semiconductor fabrication, MEMS/NEMS, and optoelectronic devices underscore its significance as a versatile tool in nanofabrication research and manufacturing.

Electron beam lithography (EBL) is a powerful top-down nanofabrication technique that uses a focused beam of electrons to create intricate patterns with sub-10-nanometer resolution. EBL has become an indispensable tool in nanotechnology, enabling researchers to fabricate nanostructures with precision and control. In this literature review, we will explore the key aspects of electron beam lithography, including its principles, advancements, applications, and challenges.

Principles of Electron Beam Lithography: EBL operates on the principles of direct-write lithography, where a finely focused electron beam is scanned over a resist-coated substrate to create patterns by selectively exposing and altering the resist material. The resolution of EBL is primarily determined by the interaction between the incident electrons and the resist, with smaller beam sizes allowing for higher resolution and feature sizes. Electrons can be accelerated to energies ranging from a few kiloelectron volts (keV) to several tens of kiloelectron volts, depending on the desired feature size and depth [12].

3.4 Advancements in electron beam lithography

Sub-10-nanometer resolution: Over the years, advancements in electron optics and the development of more sophisticated electron sources have pushed the resolution of EBL to below 10 nanometers. This level of precision allows researchers to explore novel nanostructures and study fundamental phenomena at the nanoscale.

Multi-beam EBL: To improve throughput and overcome the limitations of single-beam systems, multi-beam EBL systems have emerged. These systems use an array of electron beams to write multiple patterns simultaneously, significantly reducing fabrication time.

High-throughput EBL: Several strategies have been proposed to enhance the throughput of EBL systems. Parallelization techniques, such as massively parallel electron beam systems, have shown promise in speeding up nanofabrication processes while maintaining high resolution.

3.5 Applications in electron beam lithography

Nanoelectronics: EBL has been instrumental in the development of advanced nanoelectronic devices, including transistors, memory elements, and sensors. Its ability to create complex nanostructures with high precision is crucial for the miniaturization and performance improvement of electronic components.

Photonics and Plasmonics: EBL is widely used in photonics and plasmonics research to fabricate nanophotonic devices and metasurfaces. These structures can control the flow of light at the nanoscale, enabling applications in imaging, communication, and sensing.

Nanomaterials: EBL is utilized to create templates for nanoimprinting and nanomolding processes, enabling the fabrication of nanostructured materials with tailored properties. It has also been employed to produce nanopatterned substrates for cell adhesion studies and tissue engineering applications.

3.6 Challenges and future directions

Despite its significant contributions to nanofabrication, EBL faces several challenges that researchers are actively addressing. *Throughput and Fabrication Time:* The serial nature of EBL can lead to long fabrication times, especially when dealing with large areas. Continued efforts to improve throughput and parallelization are ongoing.

Cost: EBL systems are expensive to acquire and maintain, limiting their accessibility to some research groups and institutions.

Proximity Effects: Electron scattering and backscattering can cause proximity effects, leading to feature size variations and edge roughness. Strategies such as dose modulation and correction algorithms are employed to mitigate these effects.

Electron beam lithography is a cornerstone technique in top-down nanofabrication, offering unparalleled resolution and control at the nanoscale. Its applications span diverse fields, including nanoelectronics, photonics, and materials science. With ongoing advancements and the development of new parallelization techniques, EBL continues to be a driving force in pushing the boundaries of nanotechnology and enabling groundbreaking research and technological innovations.

3.7 Advantages of top-down techniques

High precision: Top-down techniques offer excellent control over dimensions and placement accuracy, allowing the creation of well-defined nanostructures.

Established infrastructure: These techniques benefit from well-developed equipment and processes, making them readily accessible and compatible with existing manufacturing technologies.

Large-area patterning: Top-down techniques are wellsuited for large-scale fabrication and can produce uniform patterns over a large area.

4. Discussion

Depending on the particular needs of the application and the desired qualities of the produced nanostructures, bottom-up or top-down nanofabrication techniques are used. For best outcomes in nanomanufacturing, it is frequently used to combine the two methods to take use of their individual benefits. In conclusion, nanofabrication techniques are essential for developing nanotechnology and making it possible to create materials and devices at the nanoscale with extraordinary features. Both top-down and bottom-up approaches have advantages, and both give scientists and engineers a variety of tools to fully utilize the promise of nanotechnology across a range of businesses.

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